

MMBTH10LT1, MMBTH10-4LT1

Preferred Devices

VHF/UHF Transistor

NPN Silicon

- Device Marking: 3EM

Features

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	25	Vdc
Collector-Base Voltage	V_{CBO}	30	Vdc
Emitter-Base Voltage	V_{EBO}	3.0	Vdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board (Note 1) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	225 1.8	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 1)	$R_{\theta JA}$	556	$^\circ\text{C}/\text{W}$
Total Device Dissipation Alumina Substrate (Note 2) $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	300 2.4	mW mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient (Note 2)	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction and Storage Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

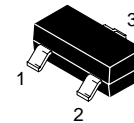
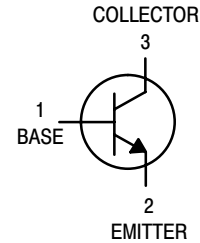
1. FR-5 = 1.0 x 0.75 x 0.062 in.

2. Alumina = 0.4 x 0.3 x 0.024 in. 99.5% alumina



ON Semiconductor®

<http://onsemi.com>



CASE 318
SOT-23
STYLE 6

ORDERING INFORMATION

Device	Package	Shipping†
MMBTH10LT1	SOT-23	3000/Tape & Reel
MMBTH10LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel
MMBTH10-4LT1	SOT-23	3000/Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

MMBTH10LT1, MMBTH10-4LT1

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage ($I_C = 1.0\text{ mA}$, $I_B = 0$)	$V_{(BR)CEO}$	25	-	-	Vdc
Collector-Base Breakdown Voltage ($I_C = 100\ \mu\text{A}$, $I_E = 0$)	$V_{(BR)CBO}$	30	-	-	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10\ \mu\text{A}$, $I_C = 0$)	$V_{(BR)EBO}$	3.0	-	-	Vdc
Collector Cutoff Current ($V_{CB} = 25\text{ Vdc}$, $I_E = 0$)	I_{CBO}	-	-	100	nAdc
Emitter Cutoff Current ($V_{EB} = 2.0\text{ Vdc}$, $I_C = 0$)	I_{EBO}	-	-	100	nAdc

ON CHARACTERISTICS

DC Current Gain ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)	MMBTH10LT1 MMBTH10-4LT1	h_{FE}	60 120	- -	- 240	-
Collector-Emitter Saturation Voltage ($I_C = 4.0\text{ mA}$, $I_B = 0.4\text{ mA}$)		$V_{CE(sat)}$	-	-	0.5	Vdc
Base-Emitter On Voltage ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$)		V_{BE}	-	-	0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain – Bandwidth Product ($I_C = 4.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$)	MMBTH10LT1 MMBTH10-4LT1	f_T	650 800	- -	- -	MHz
Collector-Base Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)		C_{cb}	-	-	0.7	pF
Common-Base Feedback Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)		C_{rb}	-	-	0.65	pF
Collector Base Time Constant ($I_C = 4.0\text{ mA}$, $V_{CB} = 10\text{ Vdc}$, $f = 31.8\text{ MHz}$)		$r_b' C_C$	-	-	9.0	ps

MMBTH10LT1, MMBTH10-4LT1

TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

($V_{CB} = 10 \text{ Vdc}$, $I_C = 4.0 \text{ mAdc}$, $T_A = 25^\circ\text{C}$)

y_{ib} , INPUT ADMITTANCE

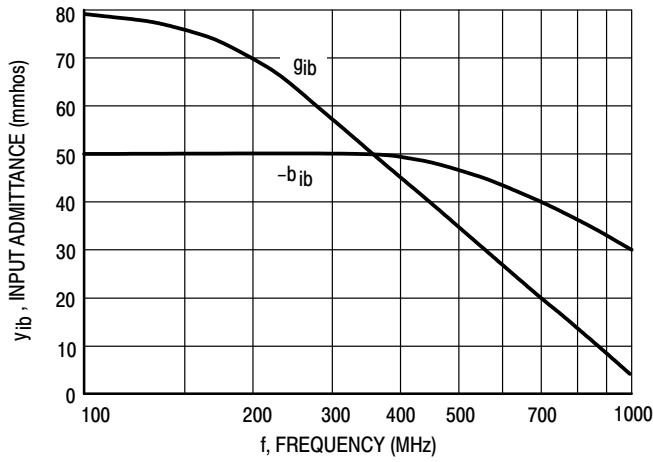


Figure 1. Rectangular Form

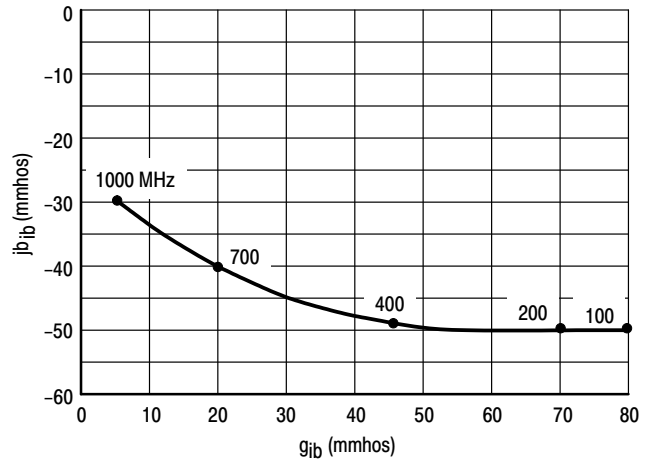


Figure 2. Polar Form

y_{fb} , FORWARD TRANSFER ADMITTANCE

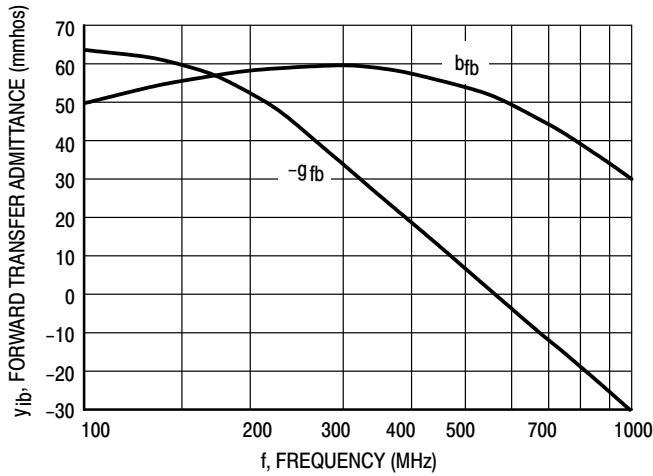


Figure 3. Rectangular Form

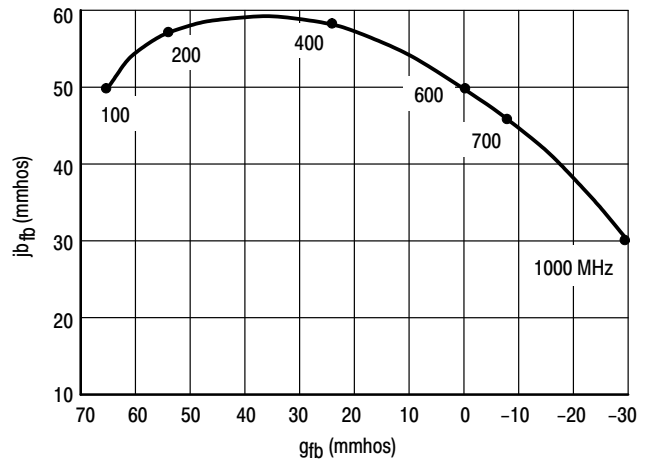


Figure 4. Polar Form

MMBTH10LT1, MMBTH10-4LT1

TYPICAL CHARACTERISTICS

COMMON-BASE y PARAMETERS versus FREQUENCY

($V_{CB} = 10 \text{ Vdc}$, $I_C = 4.0 \text{ mAdc}$, $T_A = 25^\circ\text{C}$)

y_{rb} , REVERSE TRANSFER ADMITTANCE

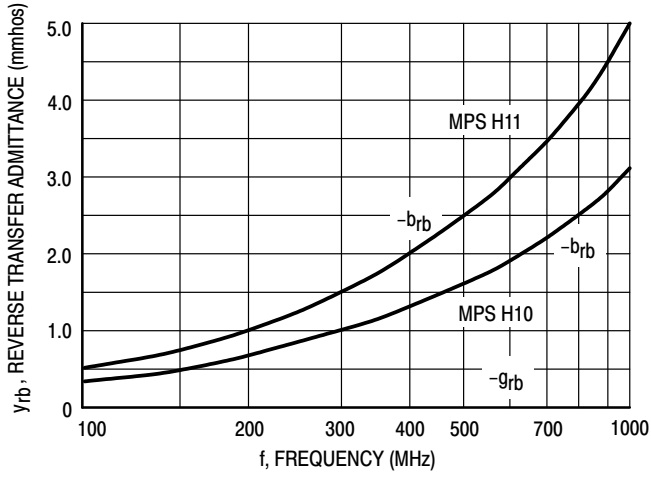


Figure 5. Rectangular Form

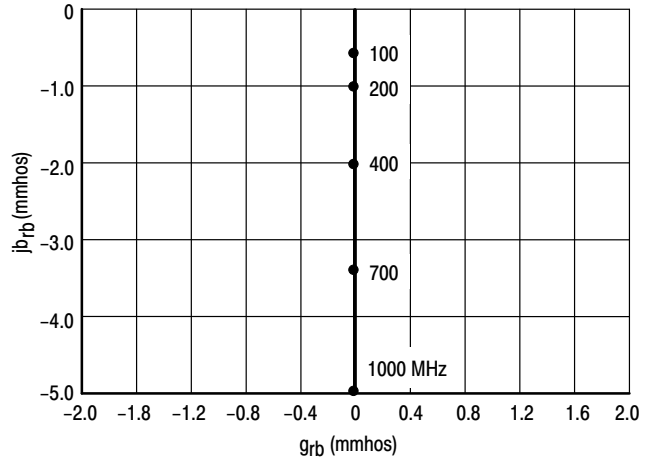


Figure 6. Polar Form

y_{ob} , OUTPUT ADMITTANCE

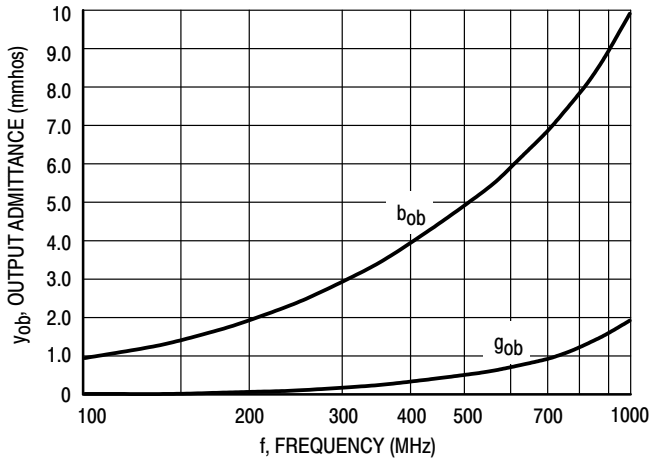


Figure 7. Rectangular Form

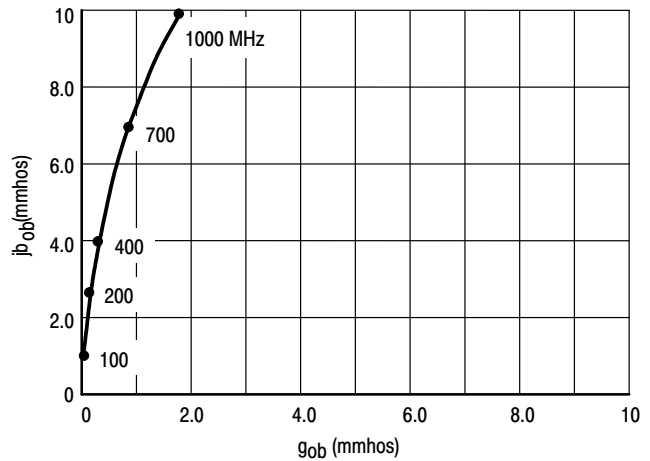
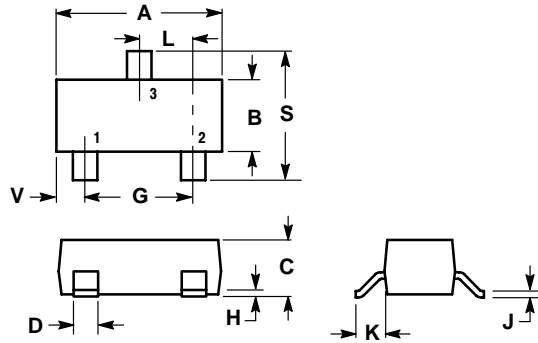


Figure 8. Polar Form

MMBTH10LT1, MMBTH10-4LT1

PACKAGE DIMENSIONS

SOT-23
(TO-236AB)
CASE 318-08
ISSUE AH



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 318-03 AND -07 OBSOLETE, NEW STANDARD 318-08.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

STYLE 6:

1. BASE
2. EMITTER
3. COLLECTOR

SOLDERING FOOTPRINT*

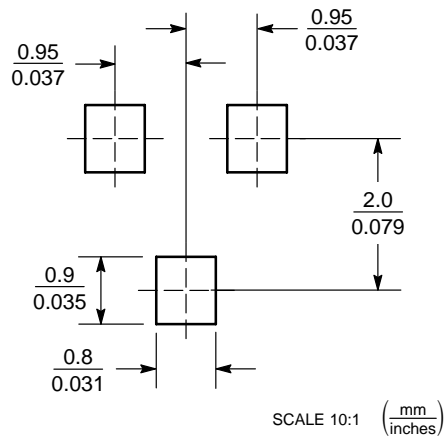


Figure 9. SOT-23

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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